version; except that marked up versions are not being supplied for any added claim or canceled claim.

21. (Amended) A conductive line comprising:

a polysilicon layer;

a metal-silicide layer against the layer of polysilicon, the metal-silicide layer comprising a Group III dopant or a Group V dopant; and

a silicon-dioxide-containing dopant barrier layer against the metal-silicide layer, the metal-silicide layer comprising the only structure directly below and against the barrier layer.

22. The conductive line of claim 21 wherein the metal-silicide layer comprises a concentration of the dopant of at least about 1×10^{18} ions/cm^3.

29. The conductive line of claim 21 wherein the silicon-dioxide-containing dopant barrier layer is elevationally above the metal-silicide layer.

30. The conductive line of claim 21 wherein the metal-silicide layer comprises an elevationally uppermost surface relative to the polysilicon layer, and wherein the silicon-dioxide-containing dopant barrier layer is against the uppermost surface.

31. The conductive line of claim 21 wherein the metal-silicide layer comprises an elevationally uppermost surface relative to the polysilicon layer, the uppermost surface having a width dimension, and wherein the silicon-dioxide-containing dopant barrier layer is against substantially the entire width of the uppermost surface.

Please add the following new claims:

32. (New) A conductive line comprising:

a polysilicon layer;

a doped metal-silicide layer against the polysilicon layer;

a silicon-dioxide-containing dopant barrier layer against the metal-silicide layer; and

the polysilicon layer, metal-silicide layer and barrier layer having aligned respective sidewalls, the aligned respective sidewalls defining an entirety of a lateral width for the conductive line.

33. (New) The conductive line of claim 32 wherein the doped metal-silicide layer comprises a Group III dopant or a Group V dopant.

34. (New) The conductive line of claim 32 wherein the silicon-dioxide-containing dopant barrier layer is against only the metal-silicide layer.

35. (New) The conductive line of claim 32 wherein the metal-silicide layer is doped to a concentration of at least about 1×10^{18} ions/cm^3.

36. (New) A conductive line comprising:

a polysilicon layer supported by a substrate;

a doped metal-silicide layer supported by the polysilicon layer; and

a silicon-dioxide-containing dopant barrier layer elevationally over the metal-silicide layer and substrate, and the barrier layer against only the metal-silicide layer with respect to the substrate and the metal-silicide layer.

37. (New) The conductive line of claim 36 wherein the doped metal-silicide layer comprises a Group III dopant or a Group V dopant.

38. (New) The conductive line of claim 36 wherein the polysilicon layer comprises a lateral width substantially equal to a lateral width of the conductive line.

39. (New) The conductive line of claim 36 wherein the metal-silicide layer is doped to a concentration of at least about 1×10^{18} ions/cm^3.

40. (New) The conductive line of claim 36 wherein the metal-silicide layer comprises a lateral width substantially equal to a lateral width of the conductive line.

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41. (New) The conductive line of claim 36 wherein the silicon-dioxide-containing dopant barrier layer comprises a lateral width substantially equal to a lateral width of the conductive line.